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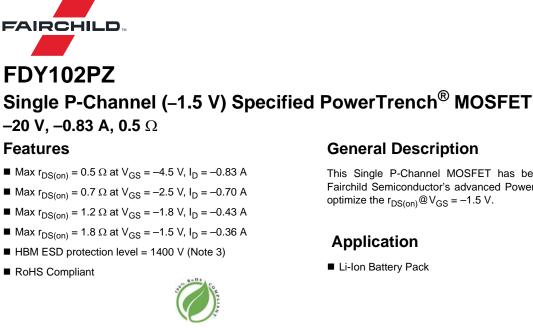


# **ON Semiconductor**®

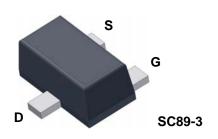
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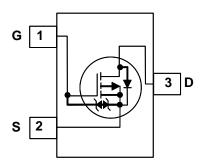
Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (\_), the underscore (\_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (\_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at <a href="mailto:www.onsemi.com">www.onsemi.com</a>. Please email any questions regarding the system integration to <a href="mailto:Fairchild\_questions@onsemi.com">Fairchild\_questions@onsemi.com</a>.

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This Single P-Channel MOSFET has been designed using Fairchild Semiconductor's advanced Power Trench process to optimize the  $r_{DS(on)}@V_{GS} = -1.5$  V.





## MOSFET Maximum Ratings T<sub>A</sub> = 25 °C unless otherwise noted

Symbol	Parameter		Ratings	Units	
V <sub>DS</sub>	Drain to Source Voltage		-20	V	
V <sub>GS</sub>	Gate to Source Voltage		±8	V	
ID	Drain Current -Continuous	(Note 1a)	-0.83	^	
	-Pulsed		-1.0	— A	
P <sub>D</sub>	Power Dissipation	(Note 1a)	0.625	14/	
	Power Dissipation	(Note 1b)	0.446	W	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range		-55 to +150	°C	

#### **Thermal Characteristics**

$R_{ ext{ heta}JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	200	°C/W
$R_{\thetaJA}$	Thermal Resistance, Junction to Ambient	(Note 1b)	280	C/VV

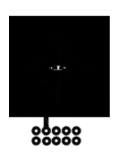
### **Package Marking and Ordering Information**

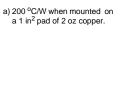
Device Marking	Device	Package	Reel Size	Tape Width	Quantity
E	FDY102PZ	SC89-3	7 "	8 mm	3000 units

April 2014

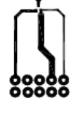
Symbol	Parameter	Test Conditions	Min	Тур	Max	Units	
Off Chara	octeristics						
BV <sub>DSS</sub>	Drain to Source Breakdown Voltage	$I_D = -250 \ \mu A, \ V_{GS} = 0 \ V$	-20			V	
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250 \ \mu$ A, referenced to 25 °C		-11		mV/°C	
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = -16 V, V_{GS} = 0 V$			-1	μΑ	
I <sub>GSS</sub>	Gate to Source Leakage Current	$V_{GS} = \pm 8 V, V_{DS} = 0 V$			±10	μA	
I <sub>GSS</sub>	Gate to Source Leakage Current	$V_{GS} = \pm 5 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$		-	±0.5	μΑ	
On Chara	cteristics (Note 2)						
V <sub>GS(th)</sub>	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = -250 \ \mu A$	-0.4	-0.7	-1.0	V	
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = -250 \ \mu\text{A}$ , referenced to 25 °C		3		mV/°C	
	Static Drain to Source On-Resistance	$V_{GS} = -4.5 \text{ V}, \text{ I}_{D} = -0.83 \text{ A}$		0.28	0.5		
		$V_{GS} = -2.5 \text{ V}, I_D = -0.70 \text{ A}$		0.36	0.7	- Ω	
(DO())		$V_{GS} = -1.8 \text{ V}, I_D = -0.43 \text{ A}$		0.47	1.2		
r <sub>DS(on)</sub>		$V_{GS} = -1.5 \text{ V}, I_D = -0.36 \text{ A}$		0.62	1.8		
		V <sub>GS</sub> = −4.5 V, I <sub>D</sub> = −0.83 A, T <sub>J</sub> =125 °C		0.39	0.85		
9 <sub>FS</sub>	Forward Transconductance	$V_{DD} = -5 \text{ V}, \text{ I}_{D} = -0.83 \text{ A}$		2		S	
Dynamic	Characteristics						
C <sub>iss</sub>	Input Capacitance			100	135	pF	
C <sub>oss</sub>	Output Capacitance	<sup>→</sup> V <sub>DS</sub> = −10 V, V <sub>GS</sub> = 0 V, →f = 1 MHz		23	35	pF	
C <sub>rss</sub>	Reverse Transfer Capacitance			18	30	pF	
Switching	g Characteristics (Note 2)						
t <sub>d(on)</sub>	Turn-On Delay Time			3.5	10	ns	
t <sub>r</sub>	Rise Time	V <sub>DD</sub> = -10 V, I <sub>D</sub> = -0.83 A		2.9	10	ns	
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{GS} = -4.5 \text{ V}, \text{ R}_{GEN} = 6 \Omega$		23	37	ns	
	Fall Time			13	23	ns	
t <sub>f</sub>				2.2	3.1	nC	
-	Total Gate Charge						
Q <sub>g</sub>	Total Gate Charge   Gate to Source Charge	$V_{DD} = -10 \text{ V}, \text{ I}_{D} = -0.83 \text{ A}$		0.3		nC	
t <sub>f</sub> Q <sub>g</sub> Q <sub>gs</sub> Q <sub>qd</sub>	° ·	$V_{DD} = -10 \text{ V}, \text{ I}_{D} = -0.83 \text{ A}$ $V_{GS} = -4.5 \text{ V}$		0.3 0.6		nC nC	
Q <sub>g</sub> Q <sub>gs</sub> Q <sub>gd</sub>	Gate to Source Charge Gate to Drain "Miller" Charge	$V_{GS} = -4.5 V$				-	
Q <sub>g</sub> Q <sub>gs</sub> Q <sub>gd</sub> Drain-Sou	Gate to Source Charge Gate to Drain "Miller" Charge urce Diode Characteristics and I	V <sub>GS</sub> = -4.5 V Maximum Rating			-0.52	-	
Q <sub>g</sub> Q <sub>gs</sub> Q <sub>gd</sub> Drain-Sou	Gate to Source Charge Gate to Drain "Miller" Charge	V <sub>GS</sub> = -4.5 V Maximum Rating de Forward Current			-0.52	nC	
Q <sub>g</sub> Q <sub>gs</sub> Q <sub>gd</sub>	Gate to Source Charge Gate to Drain "Miller" Charge urce Diode Characteristics and I Maximum Continuous Drain-Source Dioc	V <sub>GS</sub> = -4.5 V Maximum Rating de Forward Current		0.6		nC	

Notes: 1. R<sub>8JA</sub> is determined with the device mounted on a 1 in<sup>2</sup> oz. copper pad on a 1.5 x 1.5 in. board of FR-4 material. R<sub>8JC</sub> is guaranteed by design while R<sub>8JA</sub> is determined by the user's board design.

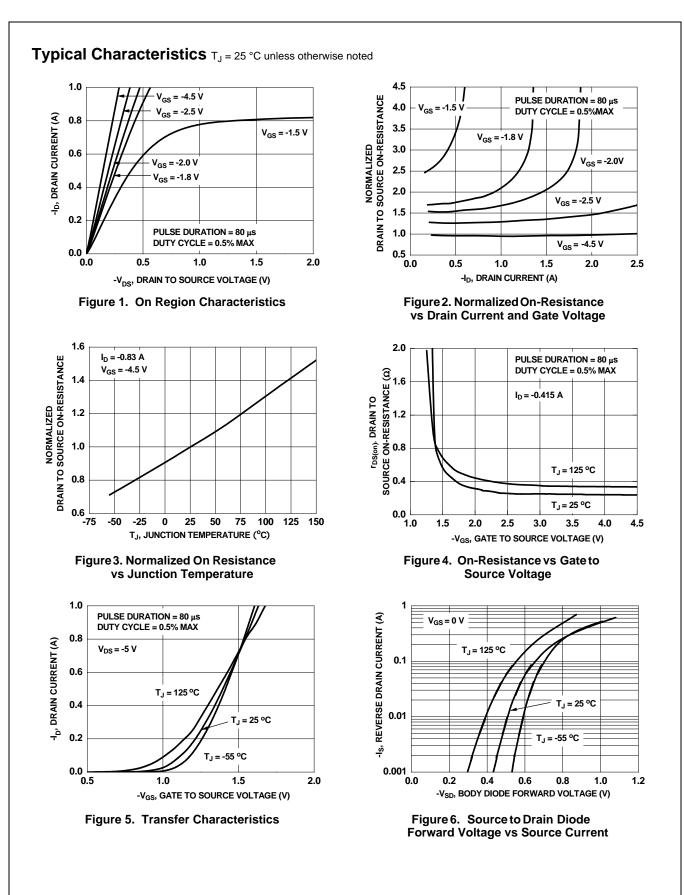




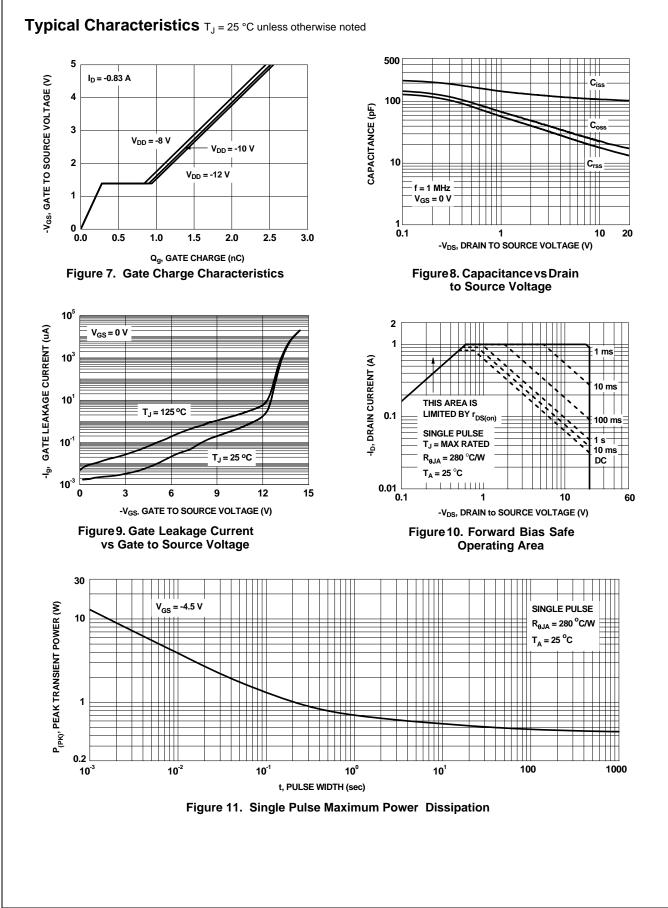
Pulse Test : Pulse Width < 300 us, Duty Cycle < 2.0%</li>
The diode connected between the gate and source serves only as protection against ESD. No gate overvoltage rating is implied.



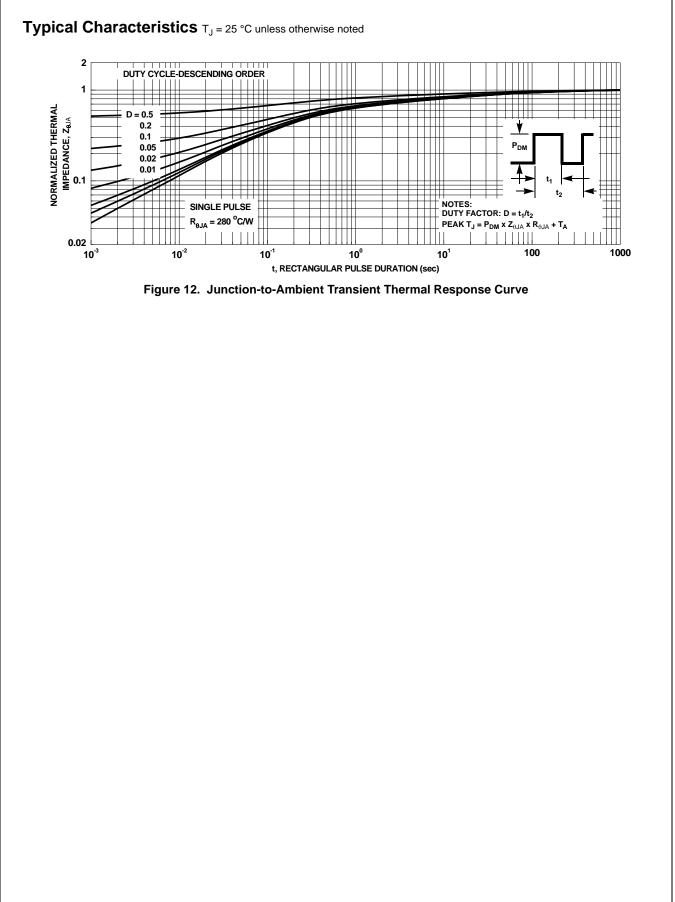
b) 280 °C/W when mounted on a minimum pad of 2 oz copper.

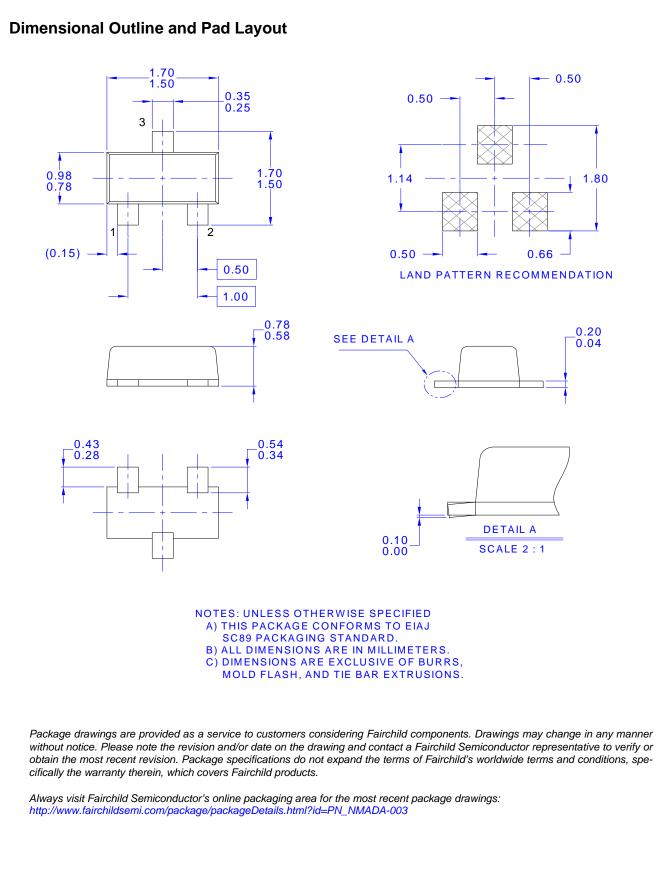


FDY102PZ Rev.B3



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Rev. 168

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